优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

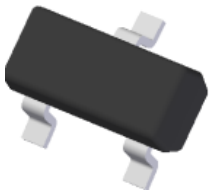
Features

- BV_{CEO} > -300V
- I_C = -0.2A Continuous Collector Current
- I_{CM} = -1A Peak Pulse Current
- Complementary NPN Type: NK-FMMT497

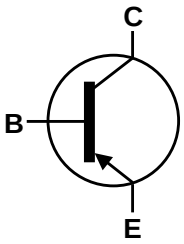
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, “Green” Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (e3)
- Weight 0.008 grams (Approximate)

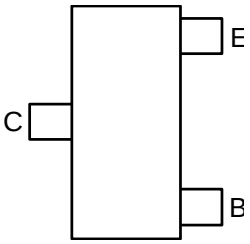
SOT23



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-0.2	A
Peak Pulse Current	I_{CM}	-1	A
Base Current	I_B	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

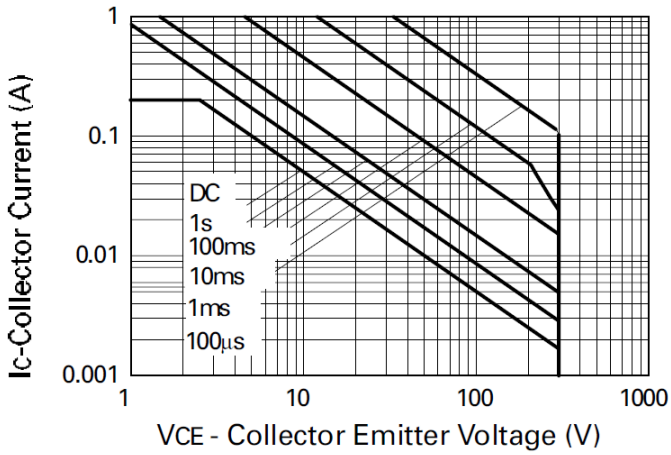
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	500	mW
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	250	°C/W
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	197	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 7)

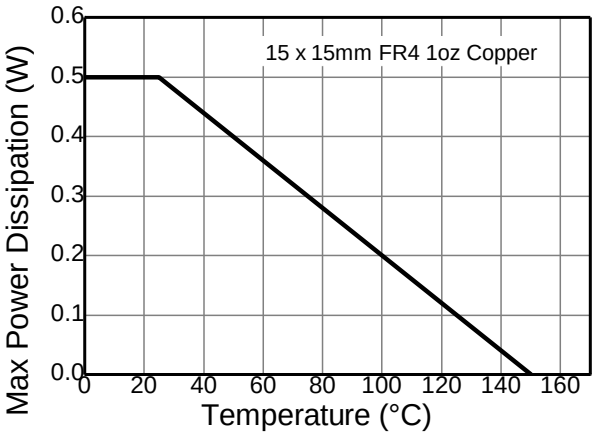
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Thermal resistance from junction to solder-point (at the end of the collector lead).
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

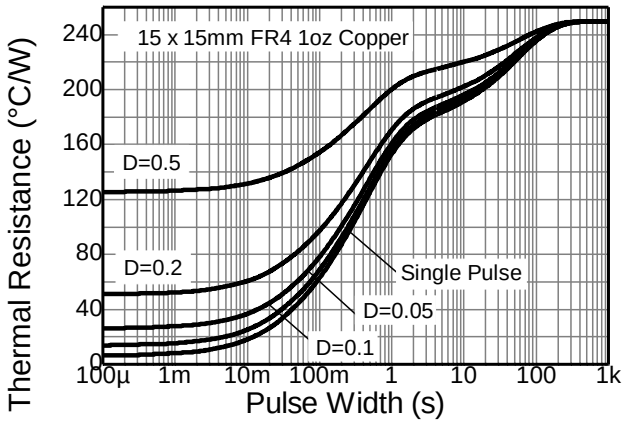
Thermal Characteristics and Derating Information



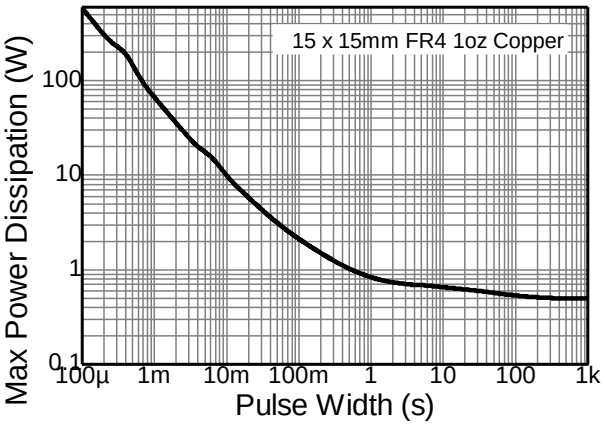
Safe Operating Area



Derating Curve



Transient Thermal Impedance



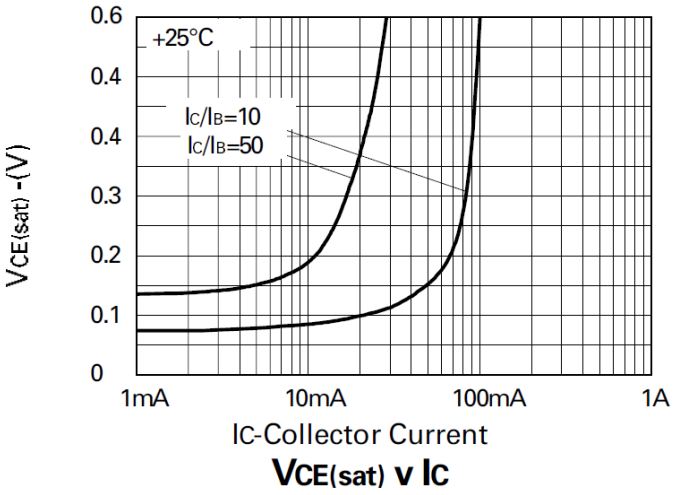
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

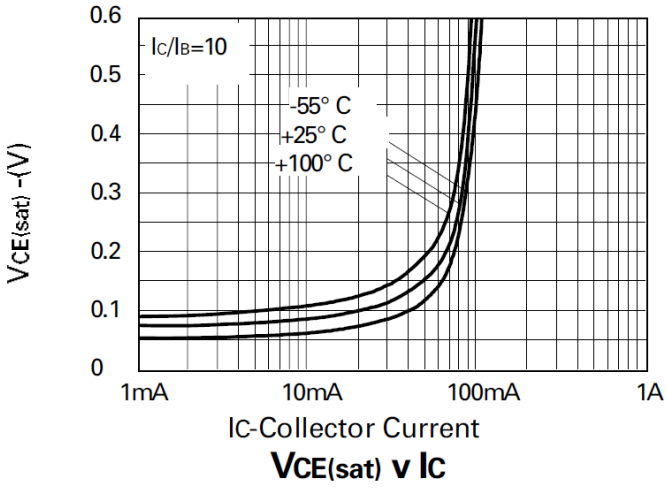
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-300	—	—	V	I_C = -100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV_{CEO}	-300	—	—	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.1	—	V	I_E = -100μA
Collector-Base Cut-Off Current	I_{CBO}	—	<1	-100	nA	V_{CB} = -250V
Emitter-Base Cut-Off Current	I_{EBO}	—	<1	-100	nA	V_{EB} = -4V
Collector-Emitter Cut-Off Current	I_{CES}	—	<1	-100	nA	V_{CE} = -250V
Static Forward Current Transfer Ratio (Note 8)	h_{FE}	100 100 100	— — —	— 300 —	—	I_C = -1mA, V_{CE} = -10V I_C = -50mA, V_{CE} = -10V I_C = -100mA, V_{CE} = -10V
Collector-Emitter Saturation Voltage (Note 8)	$V_{CE(SAT)}$	—	—	-250 -250	mV	I_C = - 50mA, I_B = -5mA I_C = - 100mA, I_B = -20mA
Base-Emitter Saturation Voltage (Note 8)	$V_{BE(SAT)}$	—	—	-1000	mV	I_C = -100mA, I_B = -20mA
Base-Emitter Turn-On Voltage (Note 8)	$V_{BE(ON)}$	—	—	-850	mV	I_C = -100mA, V_{CE} = -10V
Transition Frequency	f_T	75	—	—	MHz	V_{CE} = -10V, I_C = -50mA, f = 100MHz
Output Capacitance	C_{obo}	—	—	10	pF	V_{CB} = -10V, f = 1MHz

Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

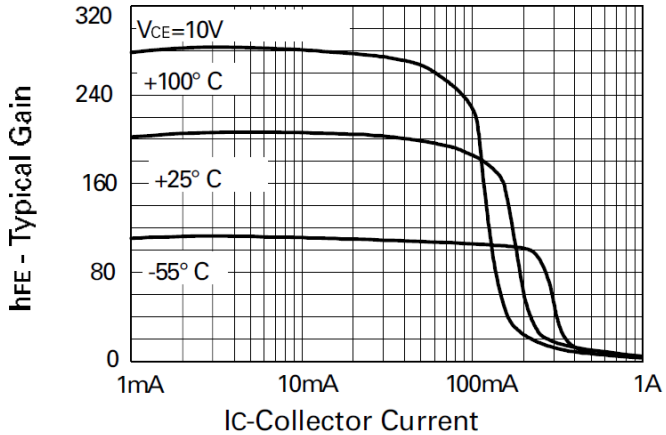
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



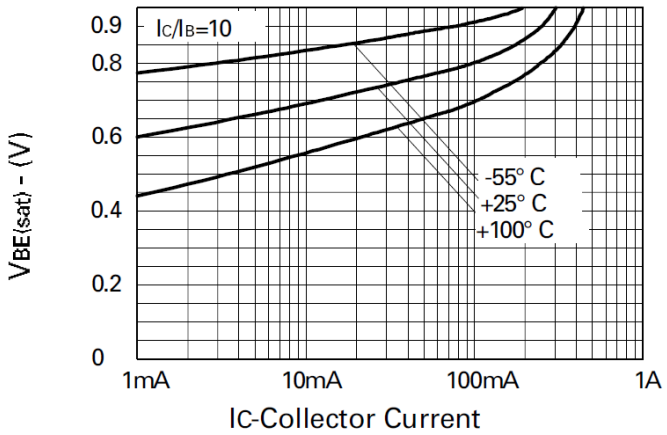
VCE(sat) v IC



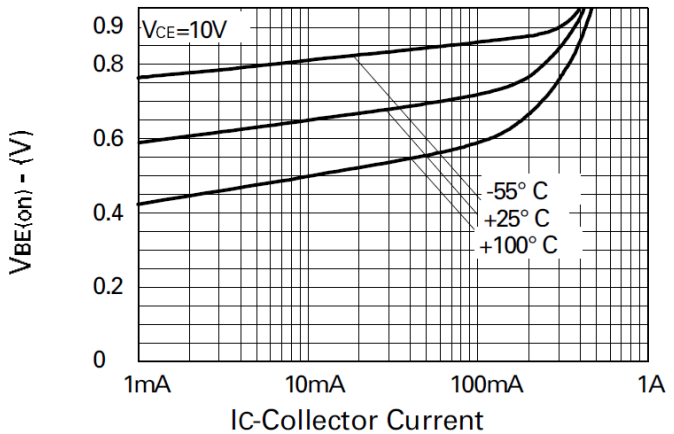
VCE(sat) v IC



hFE V IC

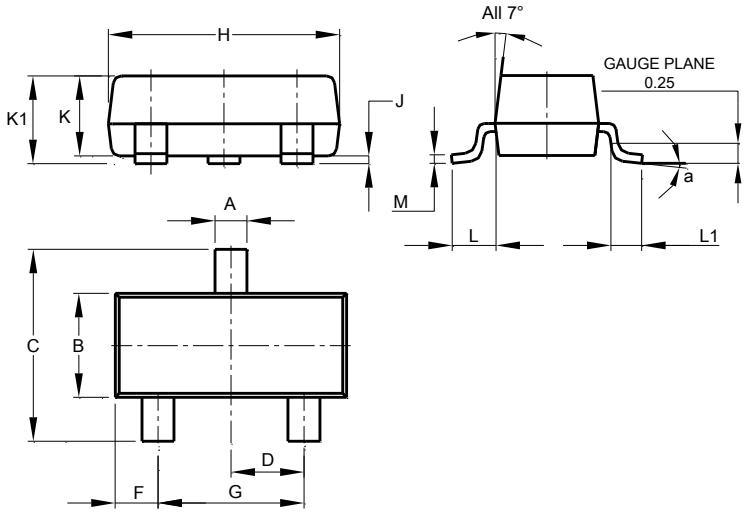


VBE(sat) v IC



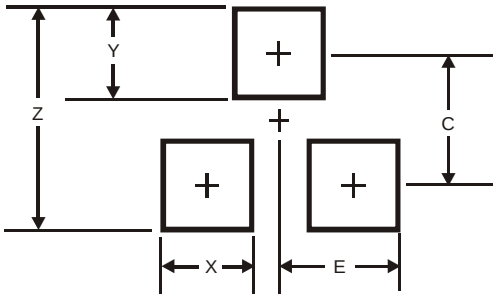
VBE(on) v IC

Package Outline Dimensions



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.